





#### 1A PNP SURFACE MOUNT TRANSISTOR

#### **Features**

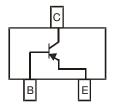
- **Epitaxial Planar Die Construction**
- Ideal for Medium Power Amplification and Switching
- High Collector Current Rating
- Complementary Version Available (DNBT8105)
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green Device" (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)







**Device Schematic** 

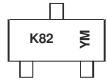
### Ordering Information (Note 3)

Part Number	Case	Packaging
DPBT8105-7	SOT23	3000/Tape & Reel

Notes:

- 1. No purposefully added lead.
  - 2. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
  - 3. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**



K82 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: S = 2005)M = Month (ex: 9 = September)

Date Code Key

Date Code Ney	_	_		_	_	_	_		_	_		
Year	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	R	S	Т	U	V	W	Х	Υ	Z	Α	В	С
				-		_			_		I	ı
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current - Continuous	Ic	-1	Α
Peak Pulse Collector Current	I <sub>CM</sub>	-2	Α

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	600	mW
Thermal Resistance, Junction to Ambient (Note 4) @ T <sub>A</sub> = 25°C	$R_{ hetaJA}$	209	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-80	_	V	$I_C = -100 \mu A$ , $I_E = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-60	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_	-100	nA	$V_{CB} = -60V, I_{E} = 0$
Collector Cutoff Current	I <sub>CES</sub>		-100	nA	V <sub>CE</sub> = -60V
Emitter Cutoff Current	I <sub>EBO</sub>		-100	nA	$V_{EB} = -4V, I_C = 0$
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h <sub>FE</sub>	100 100 80 30	300 — —		I <sub>C</sub> = -1 mA, V <sub>CE</sub> = -5V I <sub>C</sub> = -500 mA, V <sub>CE</sub> = -5V I <sub>C</sub> = -1A, V <sub>CE</sub> = -5V I <sub>C</sub> = -2A, V <sub>CE</sub> = -5V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	-0.3 -0.6	٧	$I_C = -500$ mA, $I_B = -50$ mA $I_C = -1$ A, $I_B = -100$ mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>		-1.2	V	$I_C = -1A$ , $I_B = -100mA$
Base-Emitter Turn On Voltage	V <sub>BE(ON)</sub>		-1.0	V	$I_{C} = -1A, V_{CE} = -5V$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C <sub>obo</sub>		12	pF	V <sub>CB</sub> = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	$f_{T}$	150		MHz	$V_{CE} = 10V, I_{C} = 50mA, f = 100MHz$

Notes:

Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
Short duration pulse test used to minimize self-heating effect.



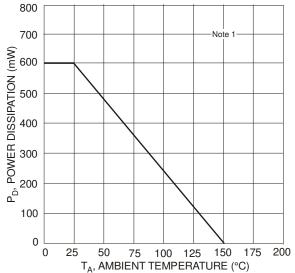


Fig. 1, Max Power Dissipation vs. Ambient Temperature

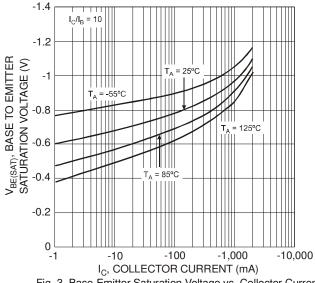


Fig. 3, Base-Emitter Saturation Voltage vs. Collector Current

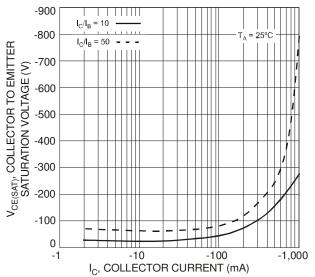
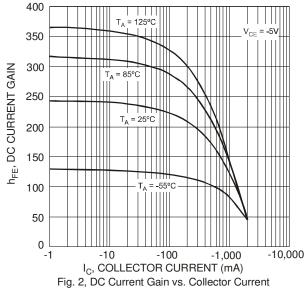


Fig. 5, Collector-Emitter Saturation Voltage vs. Collector Current



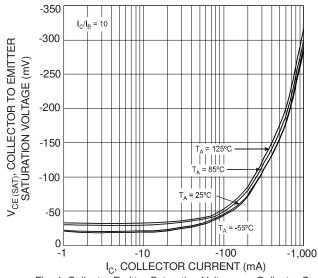


Fig. 4, Collector-Emitter Saturation Voltage vs. Collector Current

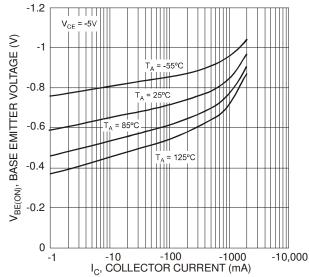
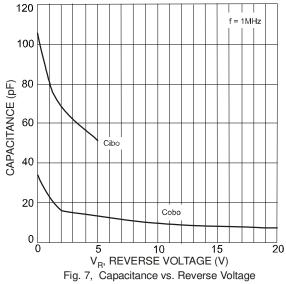
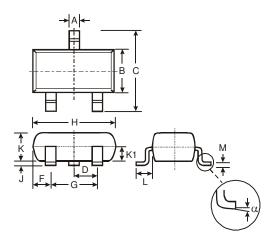


Fig. 6, Base-Emitter Voltage vs. Collector Current



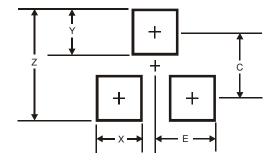


# Package Outline Dimensions



SOT-23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
7	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All Dimensions in mm						

## **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
F	1.35



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